

Silicon NPN Power Transistors

2SD1588

DESCRIPTION

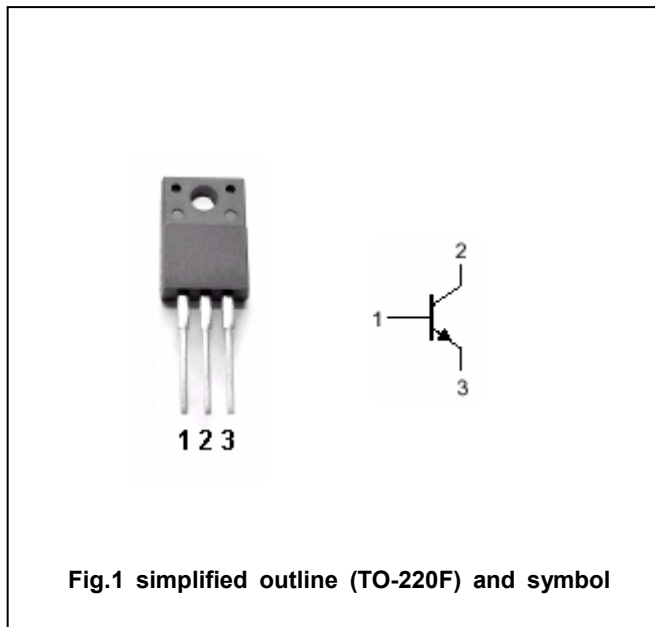
- With TO-220F package
- Complement to type 2SB1097
- Low speed switching

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector-emitter voltage	Open base	60	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current (DC)		7	A
I _{CM}	Collector current-Peak		15	A
I _B	Base current		3.5	A
P _C	Collector power dissipation	T _C =25℃	30	W
		T _a =25℃	2	
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA, I _B =0	60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =0.5A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =80V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =3A; V _{CE} =1V	40		200	
h _{FE-2}	DC current gain	I _C =5A; V _{CE} =1V	20			

◆ h_{FE-1} Classifications

R	O	Y
40-80	60-120	100-200

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PACKAGE OUTLINE

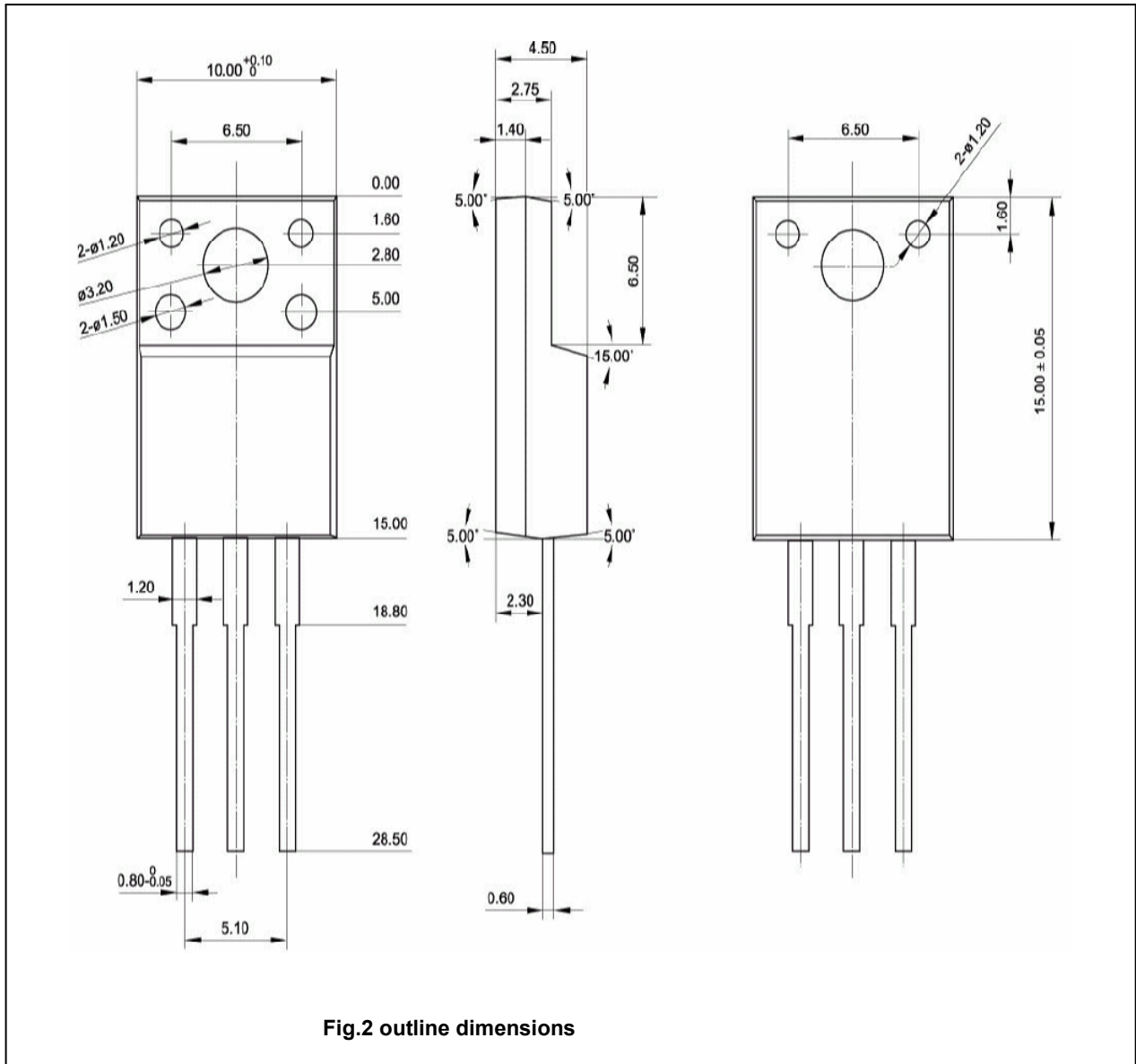


Fig.2 outline dimensions